

General Description

This Trench MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for LED Lighting and DC/DC Converters.

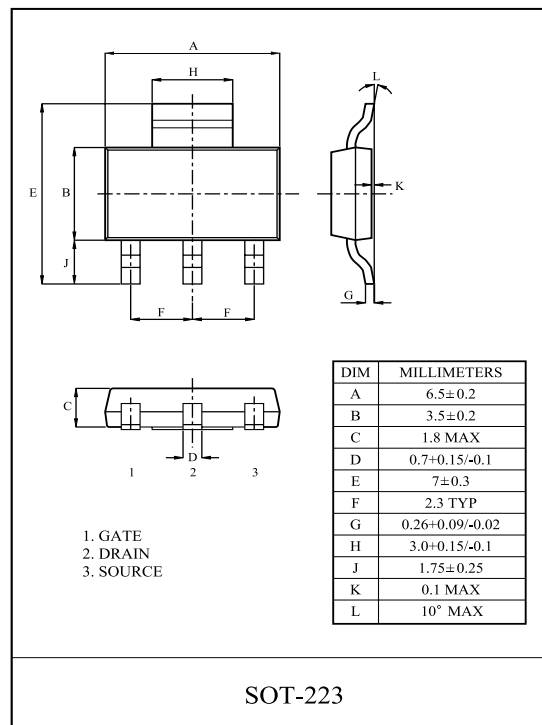
FEATURES

- $V_{DSS(Min.)} = 100V$, $I_D = 1.7A$
- Drain-Source ON Resistance : $R_{DS(ON)} = 0.36 \Omega(\text{max}) @ V_{GS} = 10V$
- $Q_g(\text{typ.}) = 4.2nC$

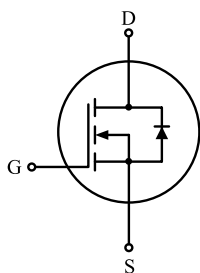
MAXIMUM RATING ($T_c = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	@ $T_c = 25^\circ C$	I_D	1.7*	A
	@ $T_c = 100^\circ C$		1.0*	
	Pulsed (Note1)	I_{DP}	6.4*	
Single Pulsed Avalanche Energy (Note 2)		E_{AS}	12.4	mJ
Repetitive Avalanche Energy (Note 1)		E_{AR}	0.1	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Drain Power Dissipation	$T_A = 25^\circ C$	P_D	2.0*	W
	Derate above $25^\circ C$		0.016	W/ $^\circ C$
Maximum Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 150	$^\circ C$
Thermal Characteristics				
Thermal Resistance, Junction-to-Ambient		R_{thJA}	62.5*	$^\circ C/W$

* : Surface Mounted on FR4 Board (50mm $\times$ 50mm, 1.0t)



PIN CONNECTION



KU3600N10W

ELECTRICAL CHARACTERISTICS (T_c=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250 μA, V _{GS} =0V	100	-	-	V
Breakdown Voltage Temperature Coefficient	Δ BV _{DSS} / Δ T _j	I _D =250 μA, Referenced to 25°C	-	0.1	-	V/°C
Drain Cut-off Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V,	-	-	10	μA
Gate Threshold Voltage	V _{th}	V _{DS} =V _{GS} , I _D =250 μA	2.0	-	4.0	V
Gate Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =0.8A	-	0.30	0.36	Ω
		V _{GS} =6V, I _D =0.8A		-	0.40	
Dynamic						
Total Gate Charge	Q _g	V _{DS} =80V, I _D =1.7A V _{GS} =10V (Note4,5)	-	4.2	5.5	nC
Gate-Source Charge	Q _{gs}		-	1.0	-	
Gate-Drain Charge	Q _{gd}		-	1.5	-	
Turn-on Delay time	t _{d(on)}	V _{DD} =50V, I _D =1.7A R _G =25Ω (Note4,5) V _{GS} =10V	-	20	-	ns
Turn-on Rise time	t _r		-	15	-	
Turn-off Delay time	t _{d(off)}		-	50	-	
Turn-off Fall time	t _f		-	10	-	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	230	320	pF
Output Capacitance	C _{oss}		-	25	-	
Reverse Transfer Capacitance	C _{rss}		-	9.0	-	
Source-Drain Diode Ratings						
Continuous Source Current	I _S	V _{GS} <V _{th}	-	-	1	A
Pulsed Source Current	I _{SP}		-	-	4	
Diode Forward Voltage	V _{SD}	I _S =1.7A, V _{GS} =0V	-	-	1.4	V
Reverse Recovery Time	t _{rr}	I _S =1.7A, V _{GS} =0V,	-	60	-	ns
Reverse Recovery Charge	Q _{rr}	dI _S /dt=100A/μs	-	0.10	-	μC

Note 1) Repetivity rating : Pulse width limited by junction temperature.

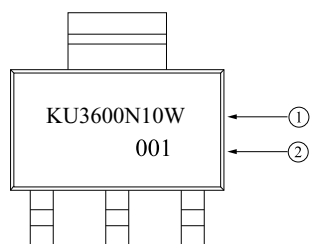
Note 2) L = 5mH, I_S=1.7A, V_{DD}=50V, R_G = 25Ω, Starting T_j = 25°C.

Note 3) I_S ≤ 1.7A, dI/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_j = 25°C.

Note 4) Pulse Test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%.

Note 5) Essentially independent of operating temperature.

Marking



① PRODUCT NAME

② LOT NO

Fig1. $I_D - V_{DS}$

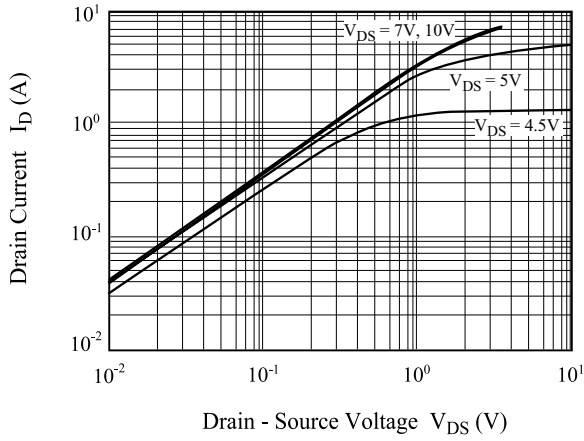


Fig2. $I_D - V_{GS}$

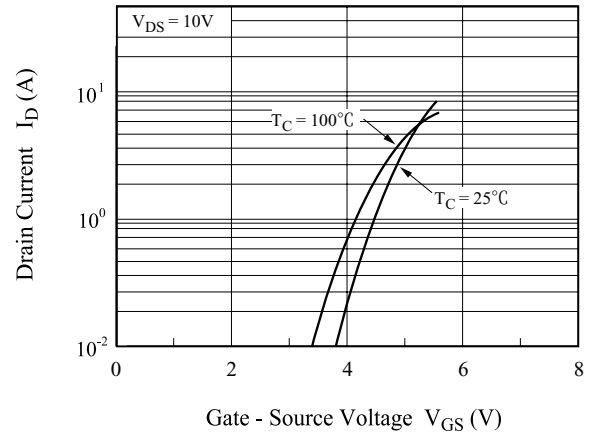


Fig3. $BV_{DSS} - T_j$

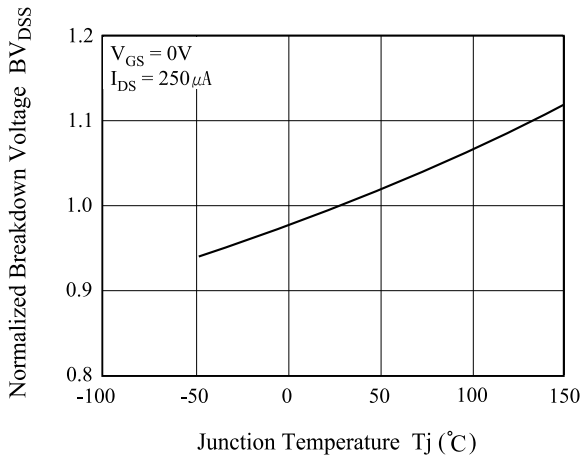


Fig4. $R_{DS(ON)} - I_D$

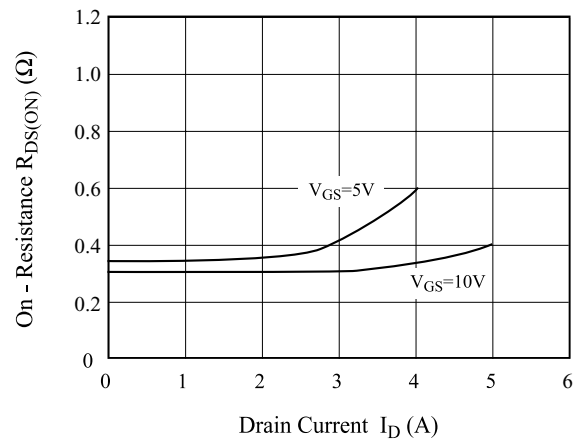


Fig5. $I_S - V_{SD}$

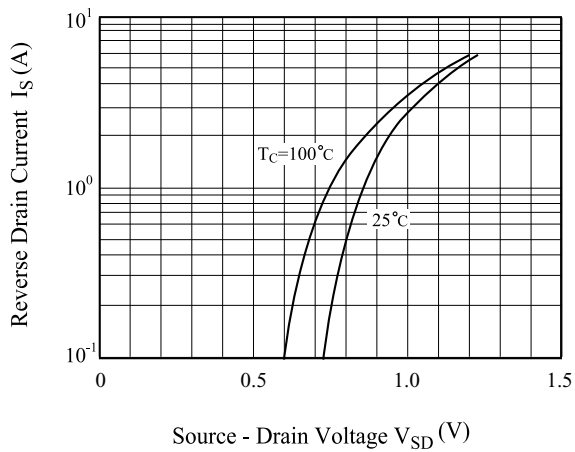


Fig6. $R_{DS(ON)} - T_j$

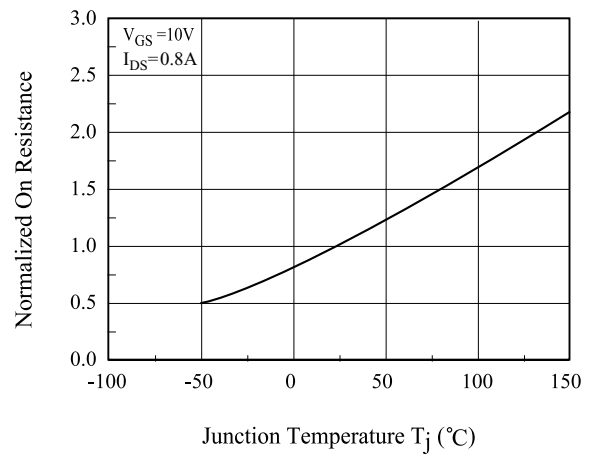


Fig 7. C - V_{DS}

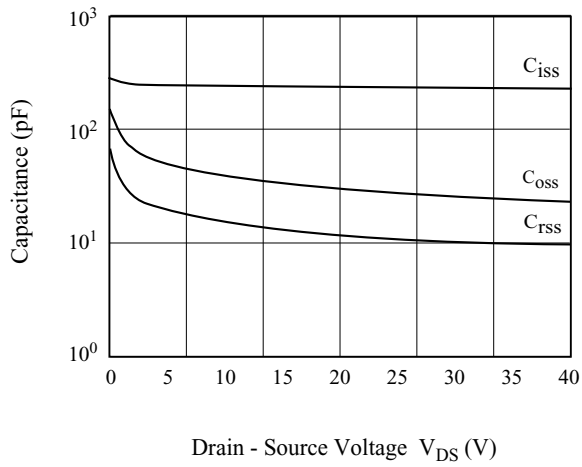


Fig8. Q_g - V_{GS}

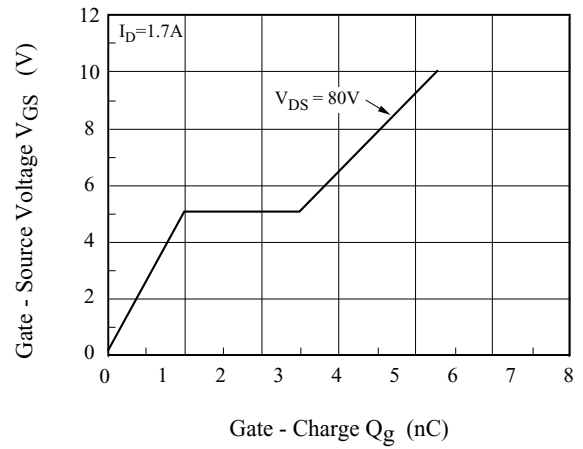


Fig9. Safe Operation Area

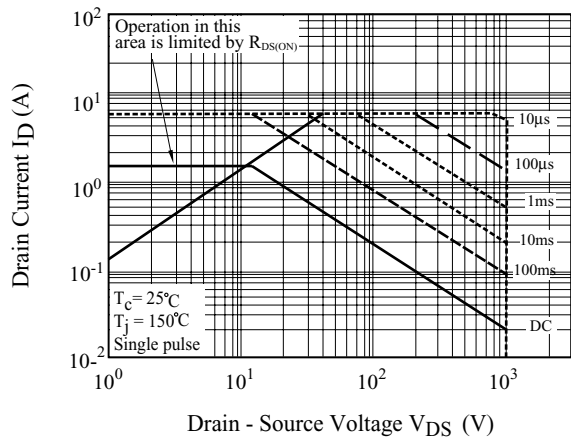


Fig10. I_D - T_j

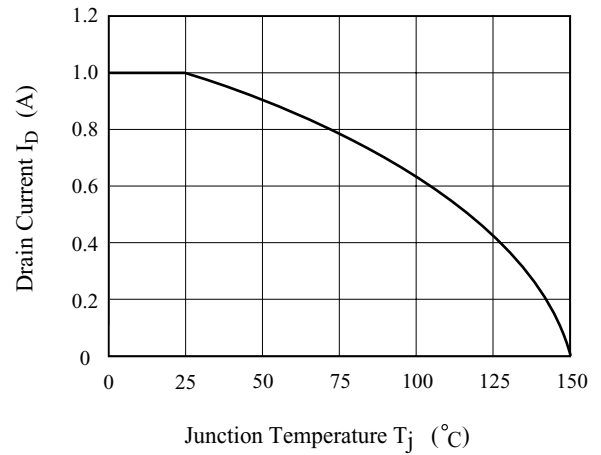


Fig11. Transient Thermal Response Curve

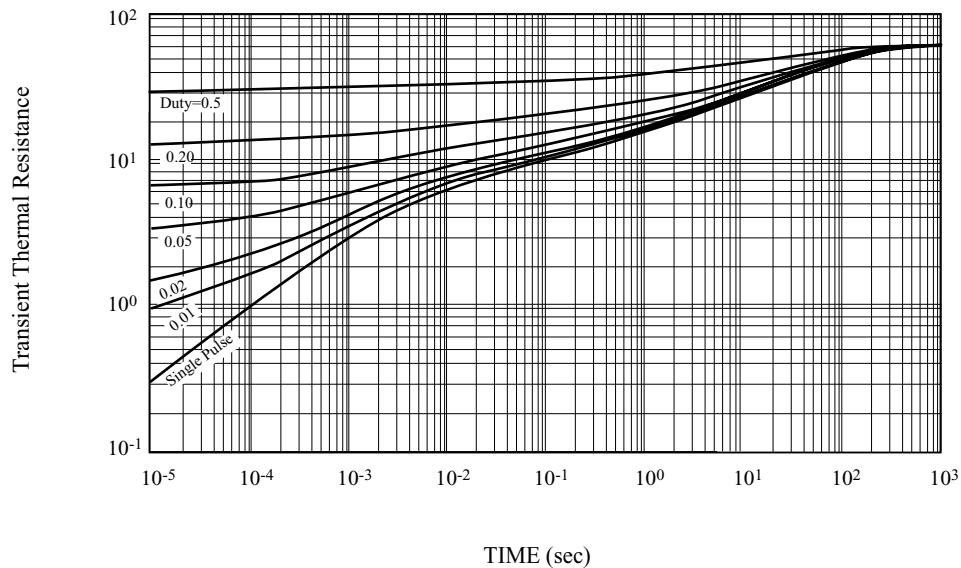


Fig12. Gate Charge

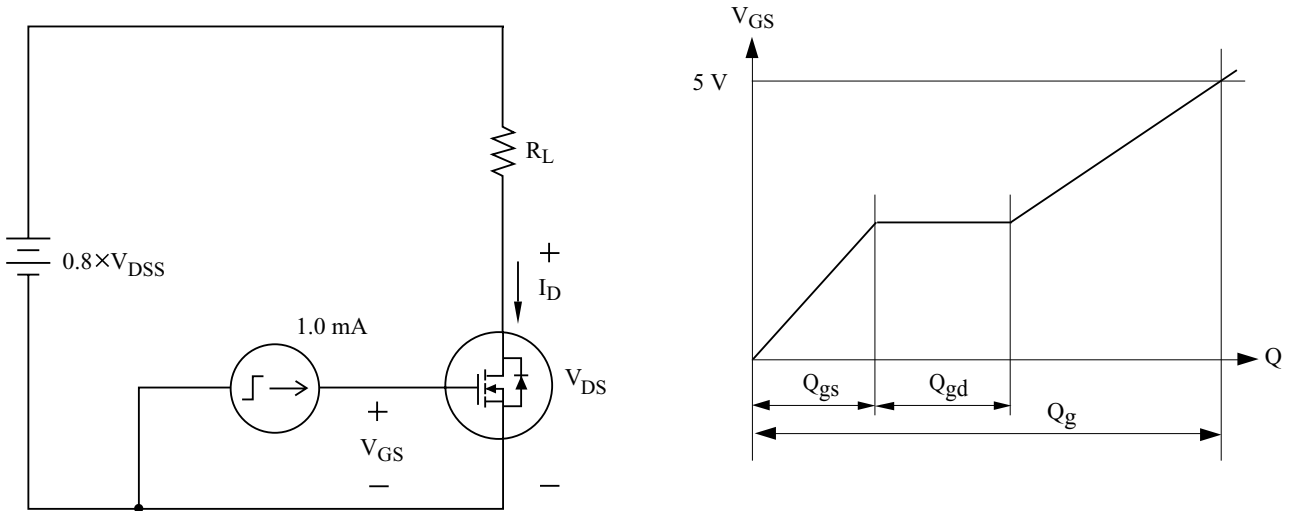


Fig13. Single Pulsed Avalanche Energy

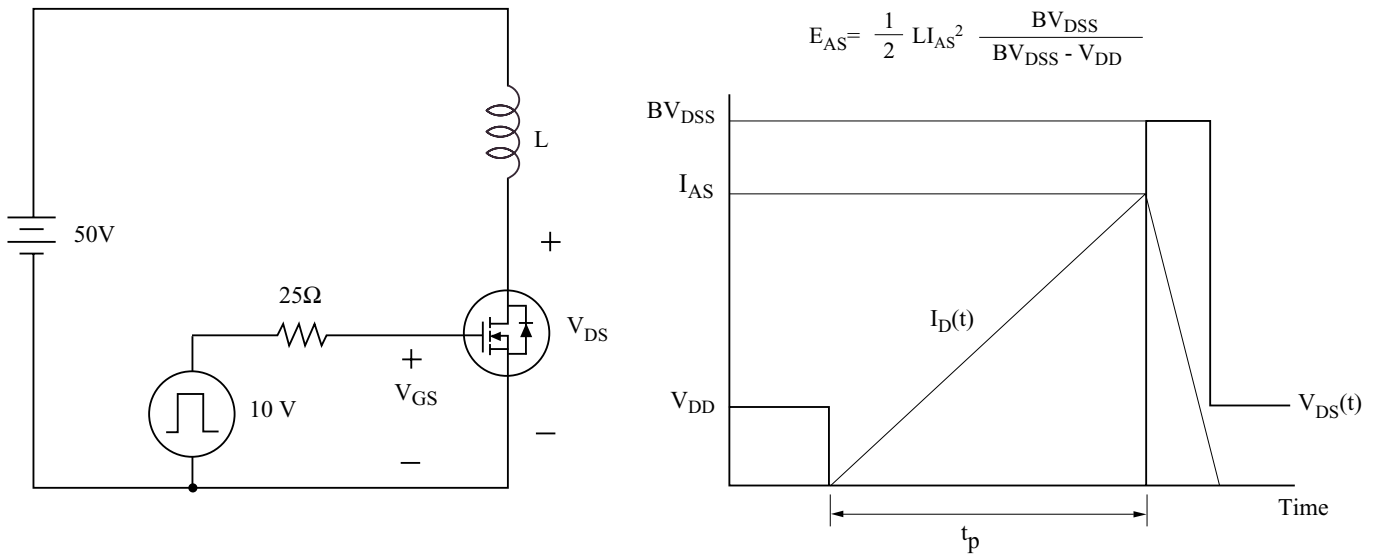


Fig14. Resistive Load Switching

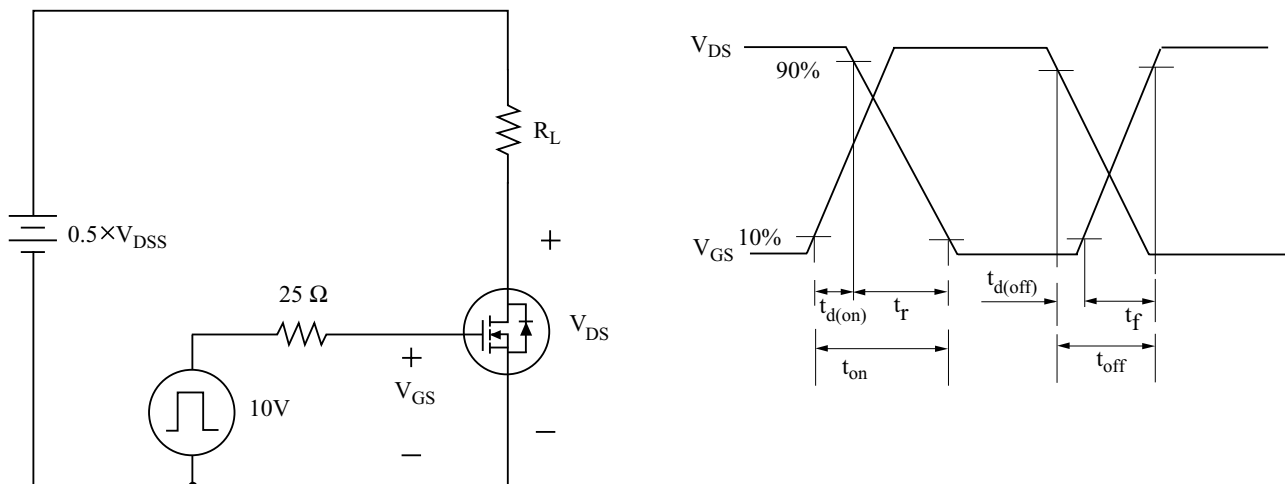


Fig15. Source - Drain Diode Reverse Recovery and dv/dt

